



迈拓电子
MAITUO ELECTRONIC

BAV19WT/BAV20WT/BAV21WT

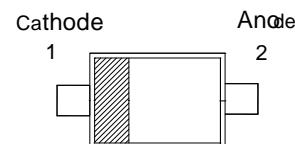


High Voltage Switching Diode

Features

- Fast switching speed
- Surface mount package ideally suited for automatic insertion

TYPE	BAV19WT	BAV20WT	BAV21WT
MARKING	A8	T2	T3



SOD-523

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage BAV19WT BAV20WT BAV21WT	V_{RRM}	120	V
		200	
		250	
Reverse Voltage BAV19WT BAV20WT BAV21WT	V_R	100	V
		150	
		200	
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	I_{FM}	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current at $t = 1 \mu\text{s}$ at $t = 1 \text{ s}$	I_{FSM}	2.5	A
		0.5	
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-65 to +150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$ BAV19WT BAV20WT BAV21WT	$V_{(BR)R}$	120	-	V
		200	-	
		250	-	
Reverse Current at $V_R = 100 \text{ V}$ at $V_R = 150 \text{ V}$ at $V_R = 200 \text{ V}$ BAV19WT BAV20WT BAV21WT	I_R	-	100	nA
		-	100	
		-	100	
Forward Voltage at $I_F = 100 \text{ mA}$ at $I_F = 200 \text{ mA}$ BAV19WT BAV20WT BAV21WT	V_F	-	1	V
		-	1.25	
		-	-	
Total Capacitance at $V_R = 0, f = 1 \text{ MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30 \text{ mA}, I_{RR} = 0.1 \times I_R, R_L = 100 \Omega$	t_{rr}	-	50	ns



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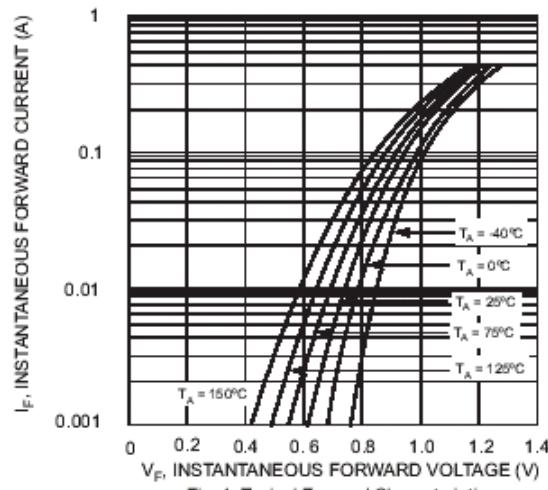


Fig. 1 Typical Forward Characteristics

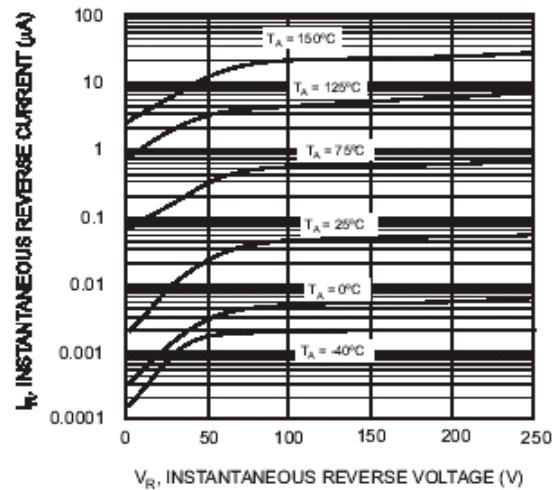


Fig. 2 Typical Reverse Characteristics

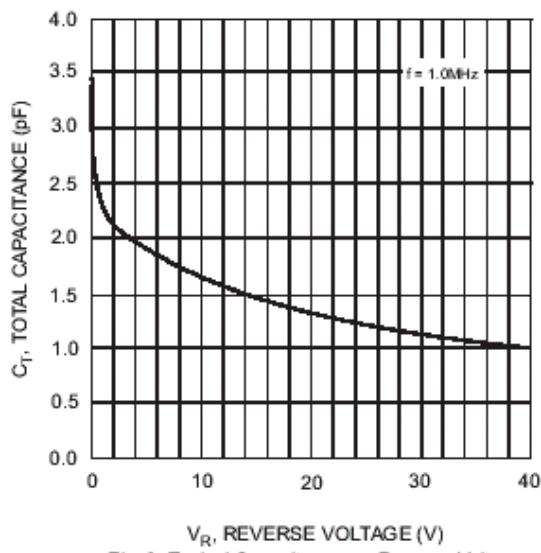


Fig. 3 Typical Capacitance vs. Reverse Voltage

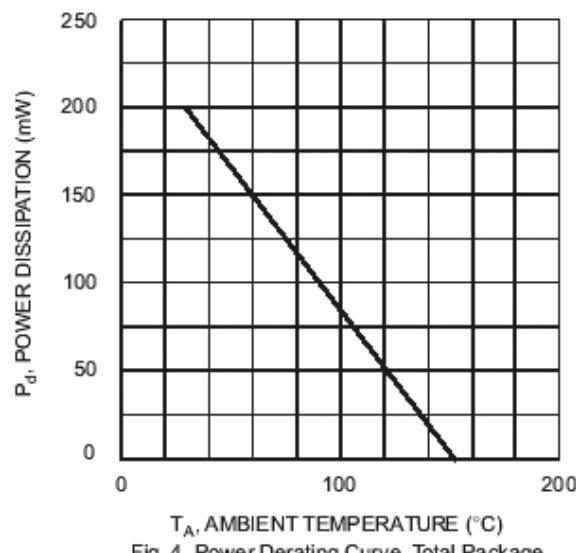


Fig. 4 Power Derating Curve, Total Package

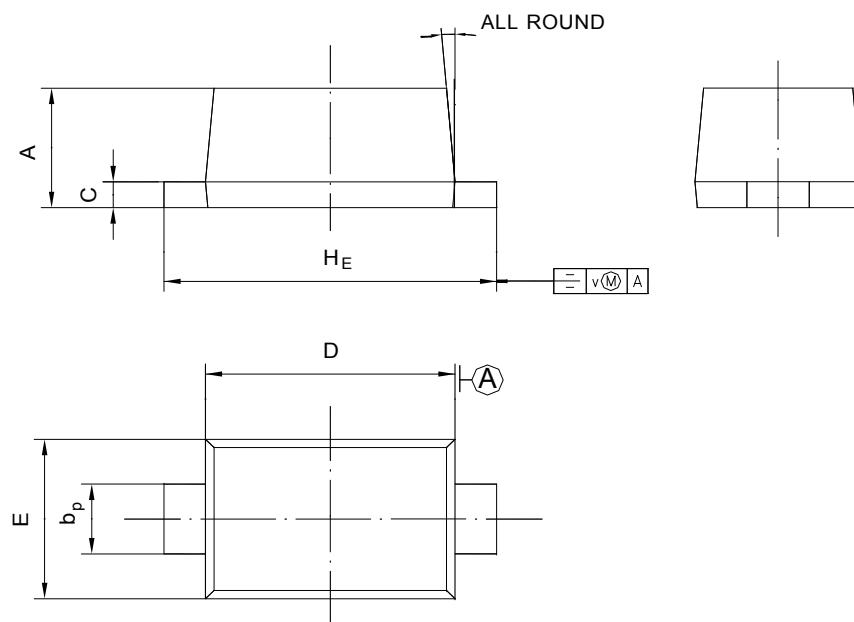


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.68	0.4	0.135	1.25	0.85	1.7	0.1	
	0.58	0.3	0.100	1.15	0.75	1.5		5°